

YJ Planar Schottky Barrier Diode Die Specification

100V 5A, 65mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB065S100SS-280A

Main Products Characterstics

Maximum Ratings			Static Electrical Characteristics (Ta = 25°C)			
Parameter	Symbol		Symbol	Value		
				Spec	Typical	
Repetitive peak reverse voltage	V _{RRM}	100 V	Reverse breakdown voltage			
Average forward current	I _{F(AV)}	5 A	I _R = 1mA	105 V	120V	
(tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	120 A	Maximum forward voltage drop			
			I _F = 5 A	V _F	0.82V	0.79V
Storage temperature range	T _{stg}	-50 to +175 °C				
						≤ 2%
Maximum operating junction temperature	T _j	175 °C		5uA	0.3uA	

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	60.6 Mils
Active Area	57 Mils
Top Metal	Ag
Back Metal	
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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